



12N50-CB

Preliminary

Power MOSFET

12A, 500V N-CHANNEL POWER MOSFET

DESCRIPTION

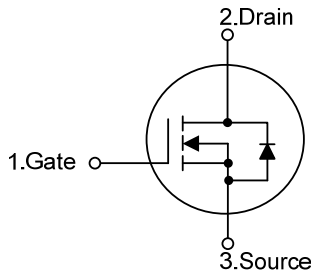
The UTC **12N50-CB** is a N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **12N50-CB** is generally applied in high efficiency switch mode power supplies, active power factor correction and electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} \leq 0.52\Omega @ V_{GS}=10V, I_D=6.0A$
- * High Switching Speed
- * 100% Avalanche Tested

SYMBOL

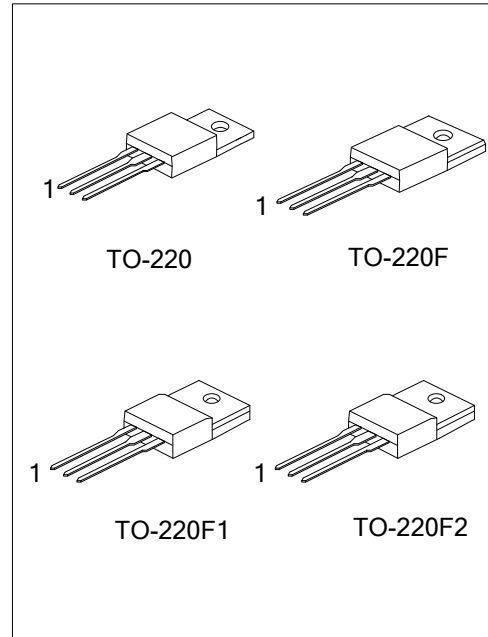


ORDERING INFORMATION

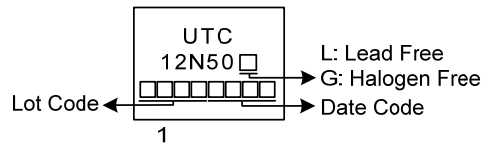
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N50L-TA3-T	12N50G-TA3-T	TO-220	G	D	S	Tube
12N50L-TF1-T	12N50G-TF1-T	TO-220F1	G	D	S	Tube
12N50L-TF2-T	12N50G-TF2-T	TO-220F2	G	D	S	Tube
12N50L-TF3-T	12N50G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>12N50G-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



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■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	115	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.5	V/ns
Power Dissipation	TO-220	P_D	160	W
	TO-220F/TO-220F1		50	W
	TO-220F2		54	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 4.8\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 12\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
Junction to Case	TO-220	θ_{JC}	0.78	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.5	$^\circ\text{C}/\text{W}$
	TO-220F2		2.31	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

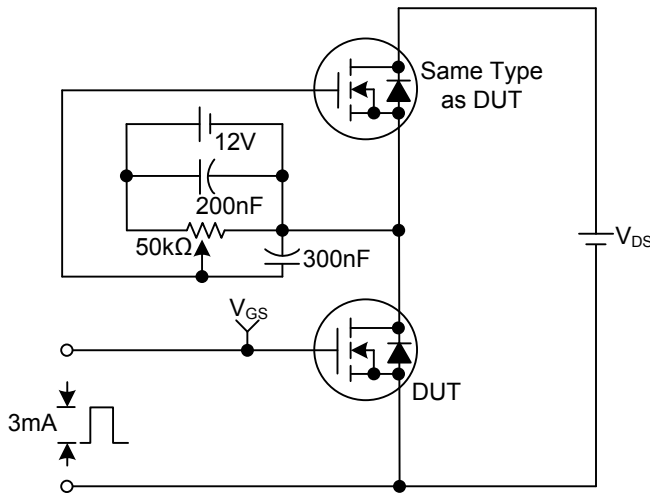
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	500			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}			+100	nA
	Reverse					
		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =6.0A			0.52	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		1360		pF
Output Capacitance	C _{OSS}			150		pF
Reverse Transfer Capacitance	C _{RSS}			6		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A I _G =100μA (Note 1, 2)		86		nC
Gate to Source Charge	Q _{GS}			9		nC
Gate to Drain Charge	Q _{GD}			8		nC
Turn-ON Delay Time (Note 1)	t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		60		ns
Rise Time	t _R			48		ns
Turn-OFF Delay Time	t _{D(OFF)}			260		ns
Fall-Time	t _F			56		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				12	A
Maximum Body-Diode Pulsed Current	I _{SM}				48	A
Drain-Source Diode Forward Voltage (Note 1)	V _{SD}	I _S =12A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)	t _{rr}	I _S =12A, V _{GS} =0V dI _F /dt=100A/μs		250		ns
Reverse Recovery Charge	Q _{rr}			3		μC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

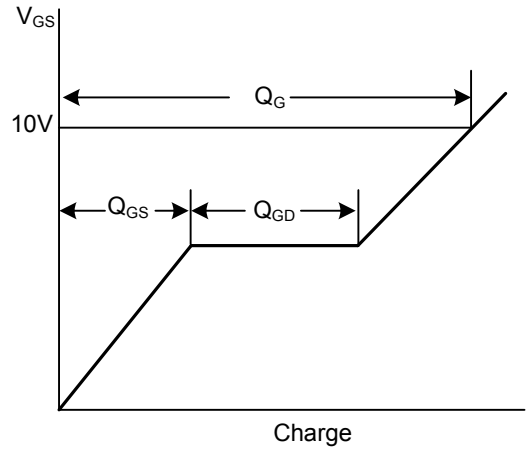
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

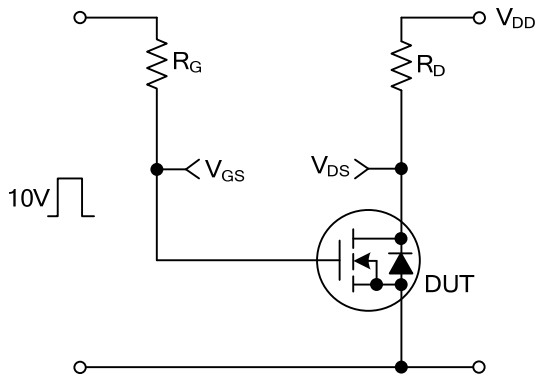
Gate Charge Test Circuit



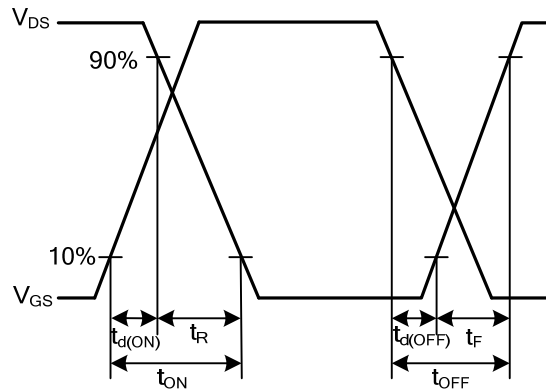
Gate Charge Waveforms



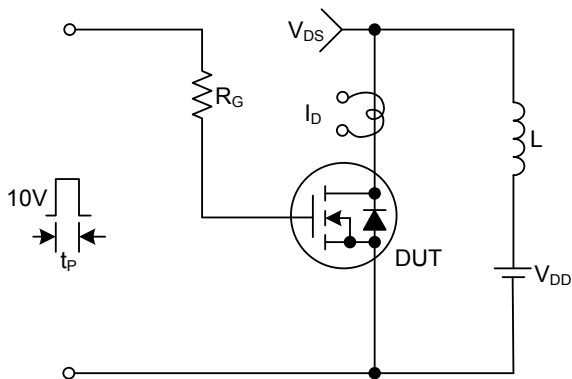
Resistive Switching Test Circuit



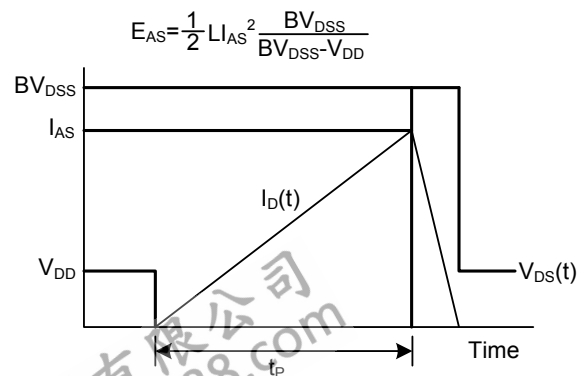
Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit

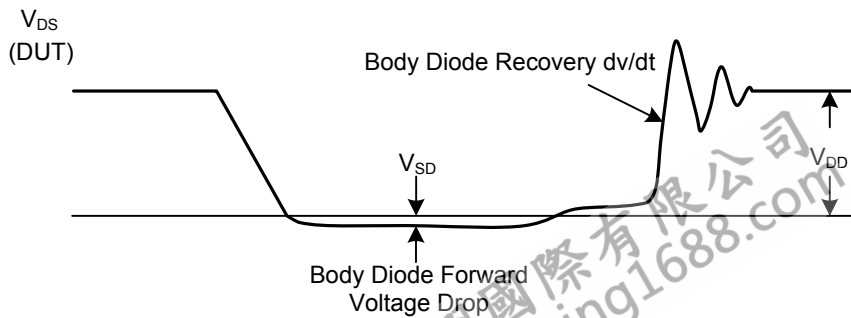
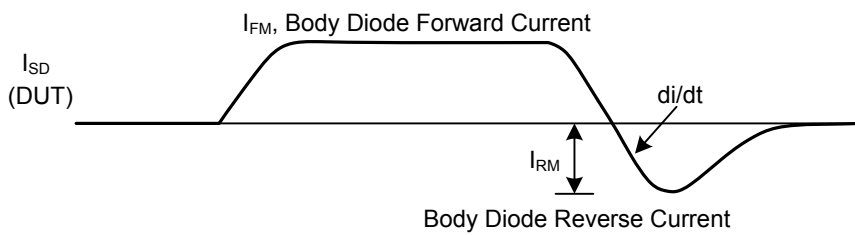
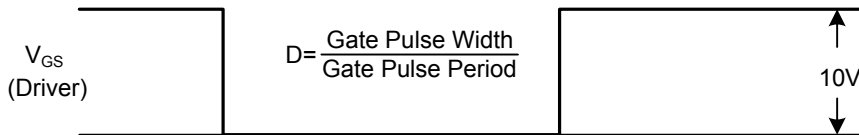
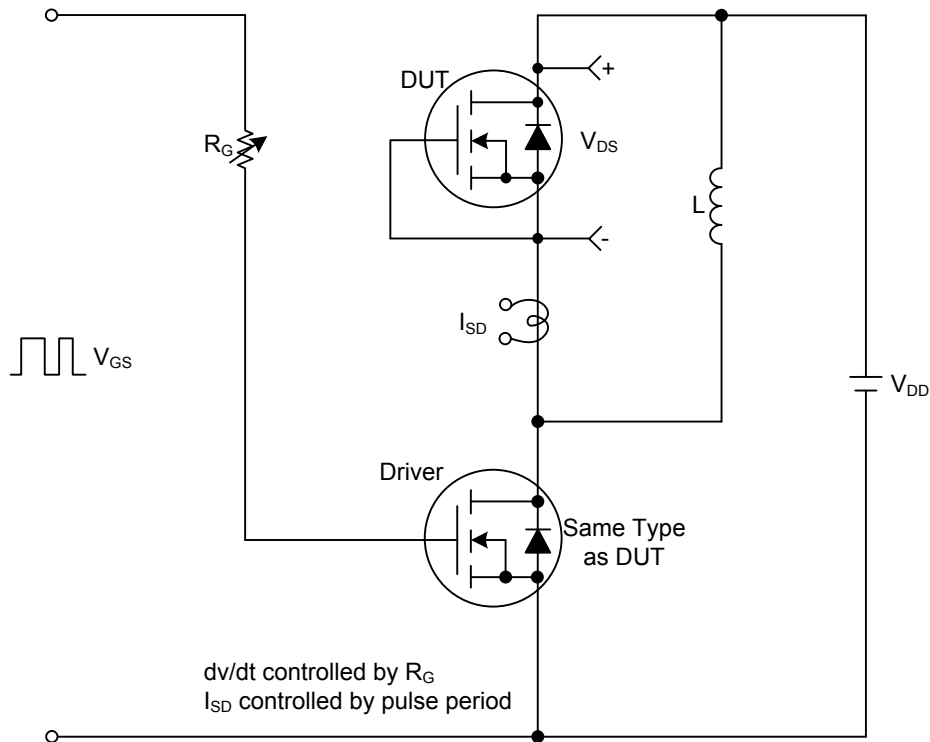


Unclamped Inductive Switching Waveforms



■ TEST CIRCUITS AND WAVEFORMS

Peak Diode Recovery dv/dt Test Circuit & Waveforms



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